

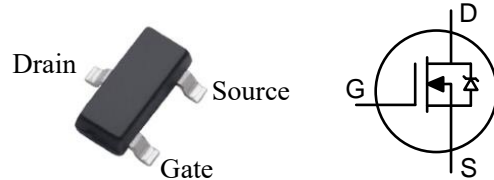
## 150V Depletion-Mode Power MOSFET

### General Features

- Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- RoHS Compliant
- Halogen-free Available

$BV_{DSX}$	$R_{DS(ON)} (MAX.)$	$I_{DSS} (MIN.)$
<b>150V</b>	<b>25Ω</b>	<b>100mA</b>

SOT-23



### Applications

- New Energy Vehicles
- Industrial Automation
- Surge Protection
- Non-isolated Linear Power Supply
- Normally-on Switches
- Linear Amplifier
- Constant Current Source
- Telecom

### Ordering Information

Part Number	Package	Marking	Remark
DMZ12C15A	SOT-23	12C15	Halogen Free

### Absolute Maximum Ratings

$T_A=25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	DMZ12C15A	Unit
$V_{DSX}$	Drain-to-Source Voltage <sup>[1]</sup>	150	V
$V_{DGX}$	Drain-to-Gate Voltage <sup>[1]</sup>	150	V
$I_D$	Continuous Drain Current	0.1	A
$I_{DM}$	Pulsed Drain Current <sup>[2]</sup>	0.4	
$P_D$	Power Dissipation	0.50	W
$V_{GS}$	Gate-to-Source Voltage	±20	V
$T_L$	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	°C
$T_J$ and $T_{STG}$	Operating and Storage Temperature Range	-55 to 150	

*Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.*

*Note: The MOSFET is sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.*

### Thermal Characteristics

Symbol	Parameter	DMZ12C15A	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	250	K/W

## Electrical Characteristics

### OFF Characteristics

 $T_J = 25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$BV_{DSX}$	Drain-to-Source Breakdown Voltage	150	--	--	V	$V_{GS} = -10\text{V}$ , $I_D = 250\mu\text{A}$
$I_{D(OFF)}$	Drain-to-Source Leakage Current	--	--	200	nA	$V_{DS} = 150\text{V}$ , $V_{GS} = -10\text{V}$
		--	--	100	$\mu\text{A}$	$V_{DS} = 150\text{V}$ , $V_{GS} = -10\text{V}$ $T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Leakage Current	--	--	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$

### ON Characteristics

 $T_J = 25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$I_{DSS}$	Saturated Drain-to-Source Current	100	--	--	mA	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	14	25	$\Omega$	$V_{GS} = 0\text{V}$ , $I_D = 50\text{mA}^{[3]}$
$V_{GS(OFF)}$	Gate-to-Source Cut-off Voltage	-2.5	--	-5.0	V	$V_{DS} = 3\text{V}$ , $I_D = 8\mu\text{A}$
gfs	Forward Transconductance	--	85	--	mS	$V_{DS} = 10\text{V}$ , $I_D = 50\text{mA}$

### Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$C_{ISS}$	Input Capacitance	--	33.2	--	pF	$V_{GS} = -10\text{V}$ $V_{DS} = 25\text{V}$ $f = 1.0\text{MHz}$
$C_{OSS}$	Output Capacitance	--	12.8	--		
$C_{RSS}$	Reverse Transfer Capacitance	--	6.5	--		
$Q_G$	Total Gate Charge	--	1.1	--	nC	$V_{GS} = -10\text{V} \sim 5\text{V}$ $V_{DD} = 25\text{V}$ , $I_D = 80\text{mA}$
$Q_{GS}$	Gate-to-Source Charge	--	0.6	--		
$Q_{GD}$	Gate-to-Drain (Miller) Charge	--	0.2	--		

### Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(on)}$	Turn-on Delay Time	--	6.4	--	ns	$V_{GS} = -10\text{V} \sim 0\text{V}$ $V_{DD} = 25\text{V}$ , $I_D = 80\text{mA}$ $R_G = 10\Omega$
$t_{rise}$	Rise Time	--	4.8	--		
$t_{d(off)}$	Turn-off Delay Time	--	5.6	--		
$t_{fall}$	Fall Time	--	35.2	--		

### Source-Drain Diode Characteristics

 $T_A = 25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Units	Test Conditions
$V_{SD}$	Diode Forward Voltage	--	--	1.2	V	$I_{SD} = 50\text{mA}$ , $V_{GS} = -10\text{V}$

NOTE:

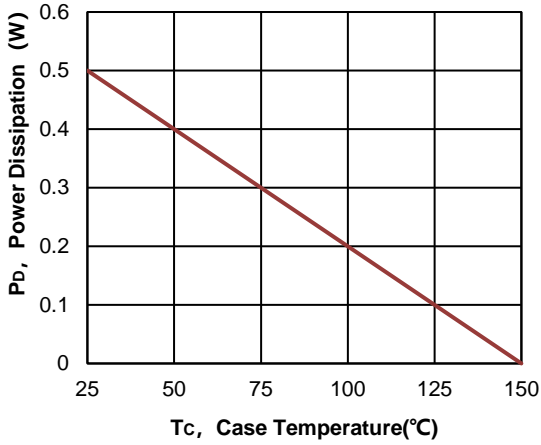
[1]  $T_J = +25^\circ\text{C}$  to  $+150^\circ\text{C}$ .

[2] Repetitive rating, pulse width limited by maximum junction temperature.

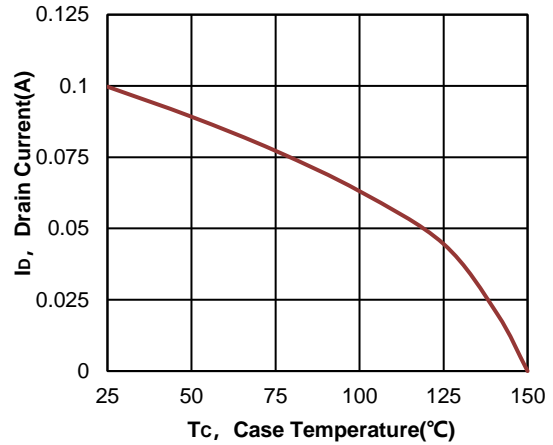
[3] Pulse width  $\leq 380\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## Typical Characteristics

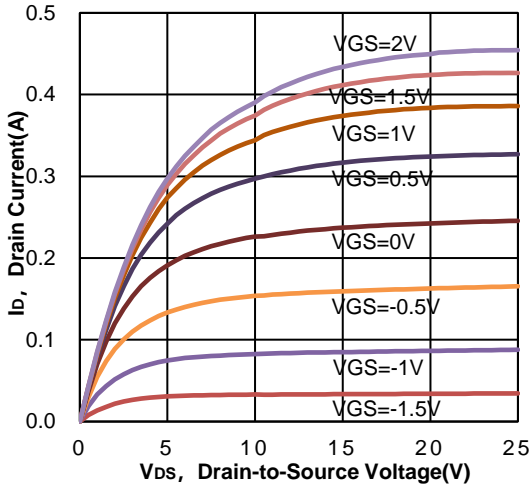
**Figure 1. Maximum Power Dissipation vs. Case Temperature**



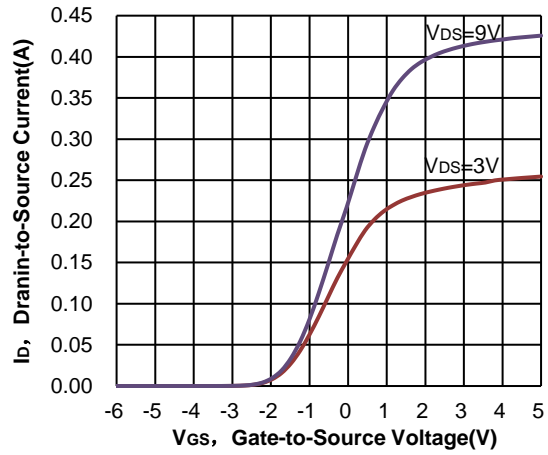
**Figure 2. Maximum Continuous Drain Current vs. Case Temperature**



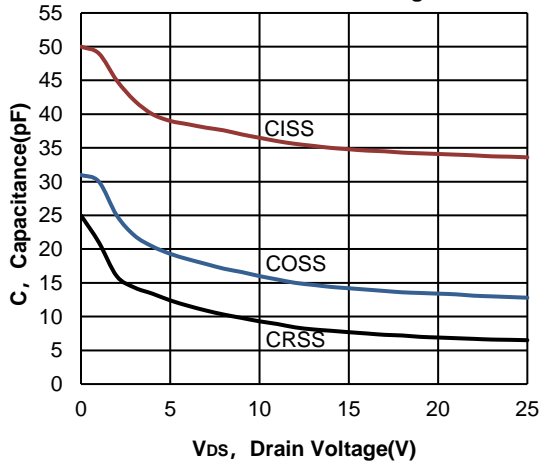
**Figure 3. Typical Output Characteristics**



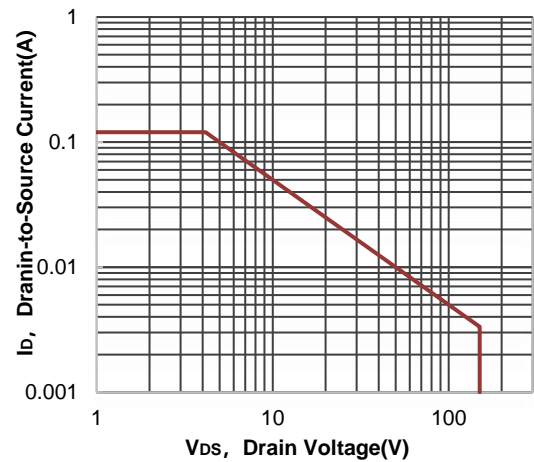
**Figure 4. Typical Transfer Characteristics**



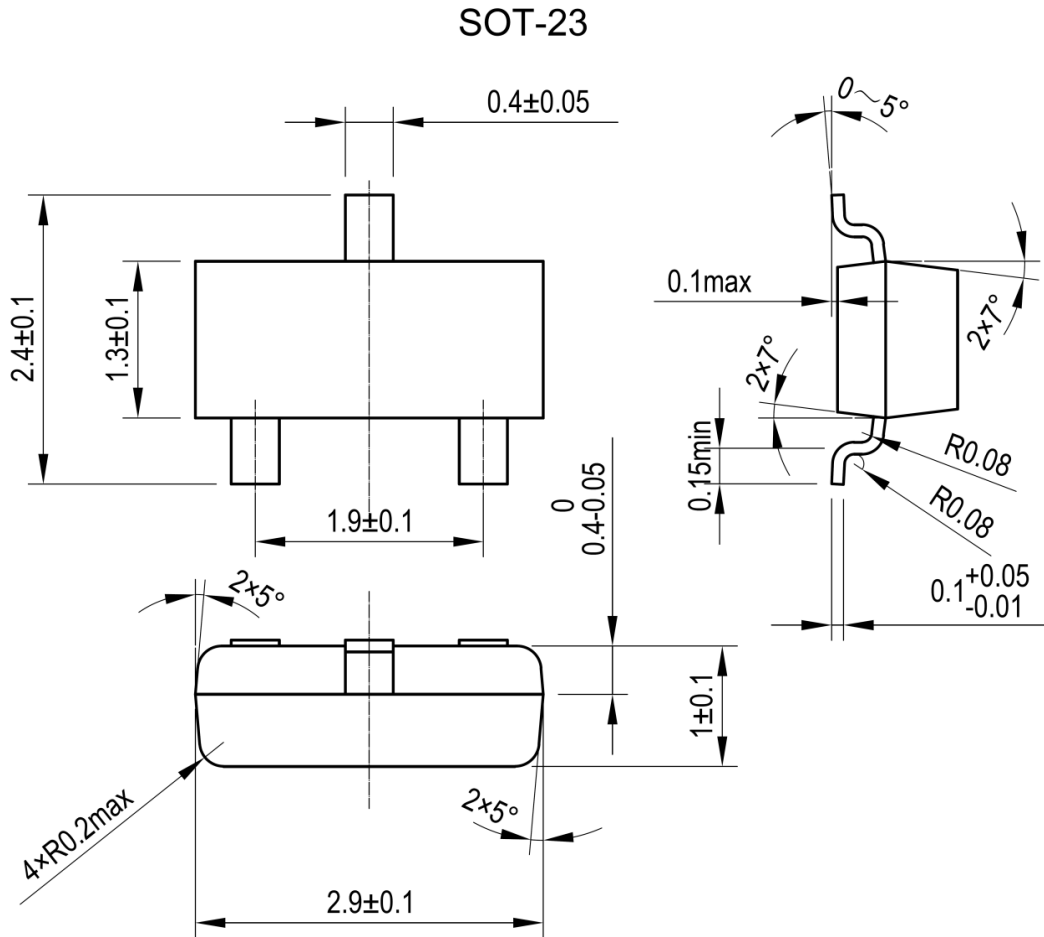
**Figure 5. Typical Capacitance vs. Drain-to-Source Voltage**



**Figure 6. Maximum Forward Safe Operating Area**



Package Dimensions





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    - b. support or sustain life,
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